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(54) SEMICONDUCTOR MEMORY DEVICE

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(57)ABSTRACT

There is provided a semiconductor memory device having improved integration and electrical characteristics. The semiconductor memory device includes a bit line extending in a first direction on a substrate, a first channel pattern disposed on the bit line, a second channel pattern disposed on the bit line and spaced apart from the first channel pattern in the first direction, a first word line disposed between the first channel pattern and the second channel pattern extends in a second direction, a second word line disposed between the first channel pattern and the second channel pattern, extends in the second direction, and is spaced apart from the first word line in the first direction, and a first capacitor and a second capacitor disposed on and connected to the first channel pattern and the second channel pattern, respectively, wherein each of the first channel pattern and the second channel pattern includes a first metal oxide pattern including indium (In), gallium (Ga) and tin (Sn), and a position of a peak of tin is different from a position of a peak of gallium in a spatial composition distribution of the first metal oxide pattern.

